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Docket No. 740756-2205  
Application Serial No. 09/651,889

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Conc'd

2. (Thrice Amended) A semiconductor device comprising a TFT containing an active layer having a channel forming region,

wherein a portion of the channel forming region is convexed or concaved in a channel width direction,

wherein zero or one grain boundary is contained in the channel forming region.

3. (Thrice Amended) A semiconductor device comprising a TFT containing an active layer having a channel forming region,

wherein a portion of the channel forming region is convexed or concaved in a channel width direction,

wherein the number of grain boundaries crossing the channel forming region in the width direction of the channel is zero or one.

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11. (Twice Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,

wherein a portion of said channel forming region is convexed in a direction perpendicular to a channel length direction.

12. (Twice Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,

wherein a portion of said channel forming region is concaved in a direction perpendicular to a channel length direction.

13. (Twice Amended) A semiconductor device comprising:

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a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein a portion of said channel forming region is convexed in a channel width direction.

14. (Twice Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein a portion of said channel forming region is concaved in a channel width direction.

15. (Twice Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein a portion of said channel forming region is convexed in a direction perpendicular to a carrier flow direction.

16. (Twice Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate;  
a channel forming region and source and drain regions formed in said semiconductor layer; and  
wherein a portion of said channel forming region is concaved in a direction perpendicular to a carrier flow direction.